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FORM PTO 14		•		ATTY DOCKET NO. 00862.022541	APPLICATION NO. 10/091,461		
U.S. DEFARTMENT OF COMMERCE ATTEND TRADEMARK OFFICE LIST OF REFERENCES LITED BY APPLICANT(S) (Use several starts if necessary)				APPLICANT MASATAKA ITO			
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U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	SAYTA TRI	DE NUMBER	DATE	NAME	CLAS	S SUBCLASS	FILING DATE IF APPROPRIATE
SDI		5,869,387	02/09/1999	Sato et al.	438	459	03/13/1995
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Id2		05-152230	06/18/1993	Japan			Abstract
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SIX		11-265893	09/28/1999	Japan			Abstract
OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)							
STI		"Nano-Defects In Commercial Bonded SOI And SIMOX", D.K. Sadana et al., 1994 IEEE International SOI Conference Proceedings, October 1994, pp. 111-112.					
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Sheet 1 of 1

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